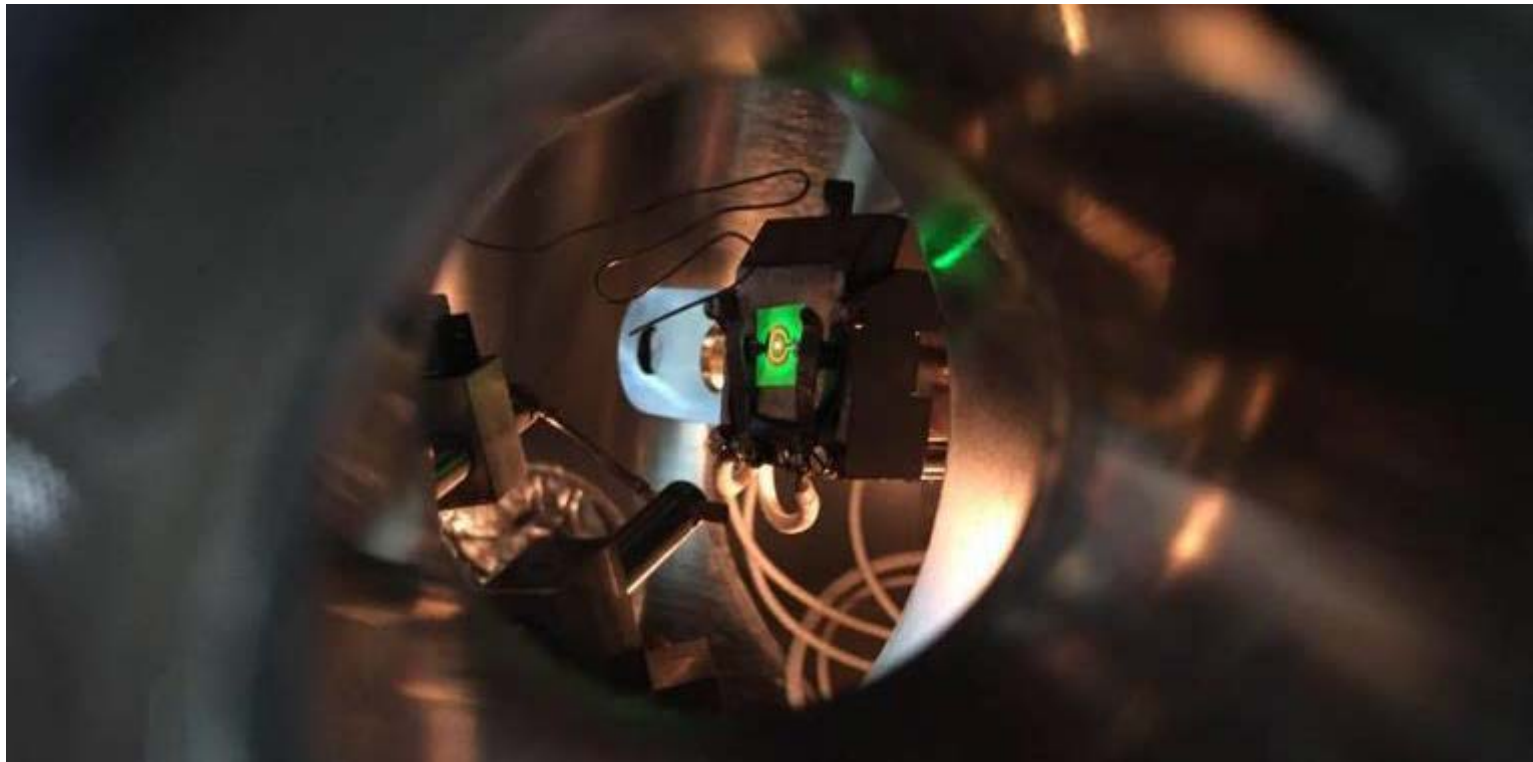


Identification and Mitigation of Droop Mechanism in GaN-Based Light Emitting Diodes (LEDs)



UC Santa Barbara

Professor James S. Speck

Speck@ucsb.edu

Project Summary

Timeline:

Start date: July 31, 2015

Planned end date: July 31, 2018

Key Milestones

1. Milestone 3.1: Determination of dominant droop mechanism in blue c-plane LEDs; date
2. Milestone 3.3: Determination of thermal droop mechanism in blue c-plane LEDs; date

Budget:

Total Project \$ to Date:

- DOE: \$935245.34
- Cost Share: \$250,000

Total Project \$:

- DOE: \$1,000,000
- Cost Share: \$250,000

Key Partners:

Cree, Inc.	

Project Outcome:

Development of a tool to directly identify the dominant non-radiative recombination mechanisms responsible for current droop, thermal droop, and the green gap.

Team



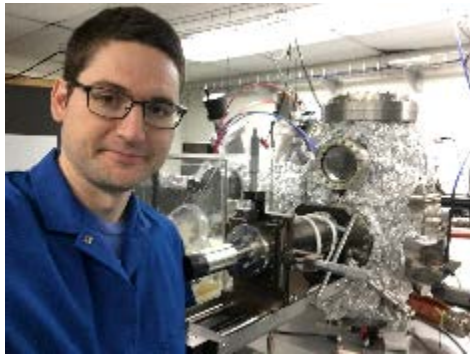
Prof. James Speck
UCSB



Prof. Claude Weisbuch
UCSB/Ecole Polytechnique



Cree, Inc.
U.S. Industry Partner



Daniel Myers
UCSB – Electroemission



Wan-Ying Ho
UCSB – Electroemission



Andrew Espenlaub
UCSB – Photocurrent

Challenge

Problem Definition:

To address the fundamental challenge of identifying the origins of current droop, thermal droop, and the green gap in state-of-the-art LEDs. Understanding the origins of LED *inefficiency* will lead to more efficient LEDs.

Target Market and Audience:

Audience: U.S.-based LED manufacturers and U.S. R&D community.

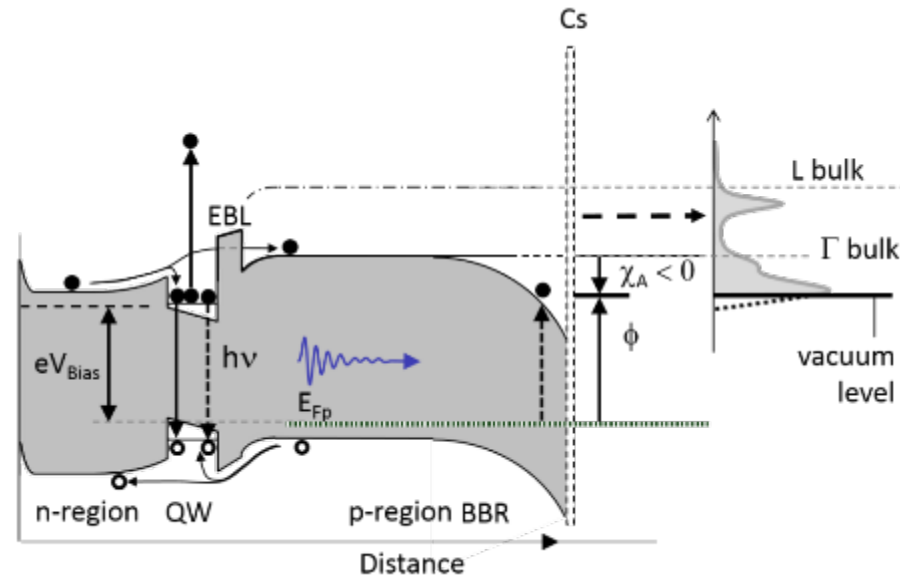
Target market: U.S. lighting market.

Approach

Measurements of droop mechanisms

- DC electrical or optical excitation (the 'ABC' model for EQE/IQE).
- Many uncertainties - some intrinsic and essential. Modeling fails to include disorder and the change of ABC parameters with injection.
- Measurements do not observe carrier dynamics inside LEDs (except time resolved emission measurements which yield dynamics, but no direct information on carriers energies).
- Carrier transfer in EL (Vampola, UCSB) could not differentiate between carrier leakage or Auger. Recent hot carrier transfer between quantum wells by Osram in PL.

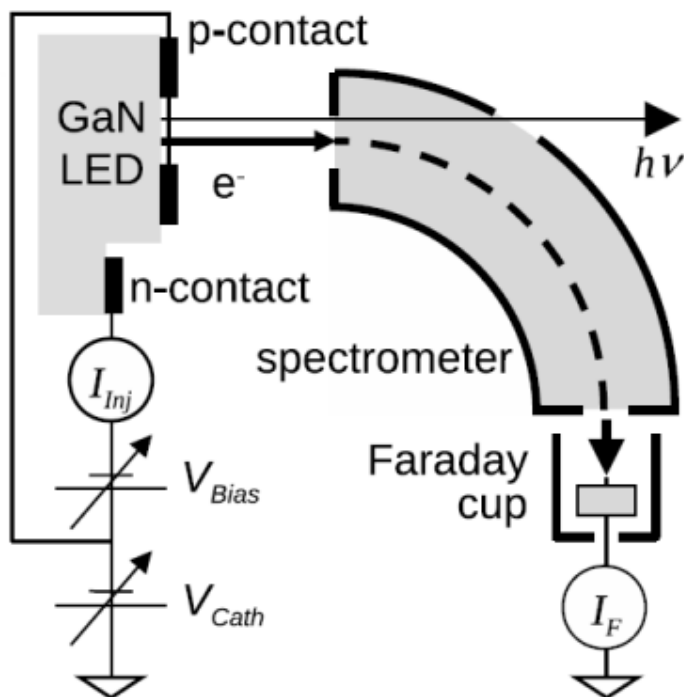
The electroemission technique



Measure electron energies and currents **inside** the LED under operation by measuring electron current and energies **outside** the LED

Approach

Low Energy Spherical Sector Analyzer



Vary V_{Cath} to sweep energy

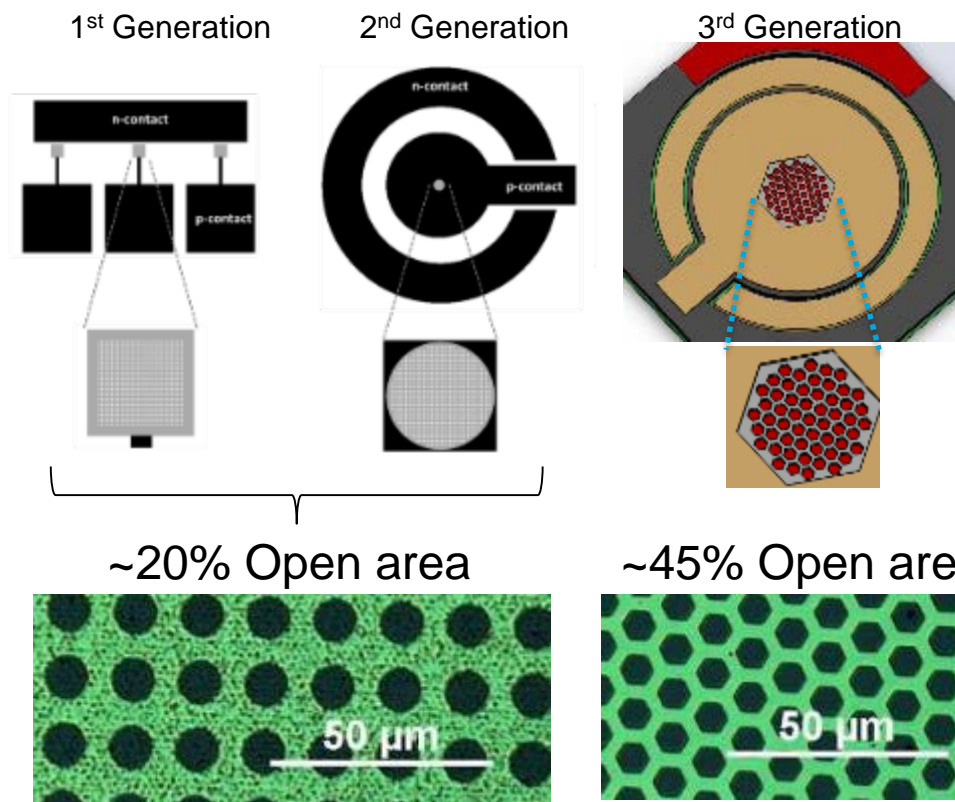
Note:

V_{Bias} relative to V_{cath}

V_{Bias} biased relative to ground

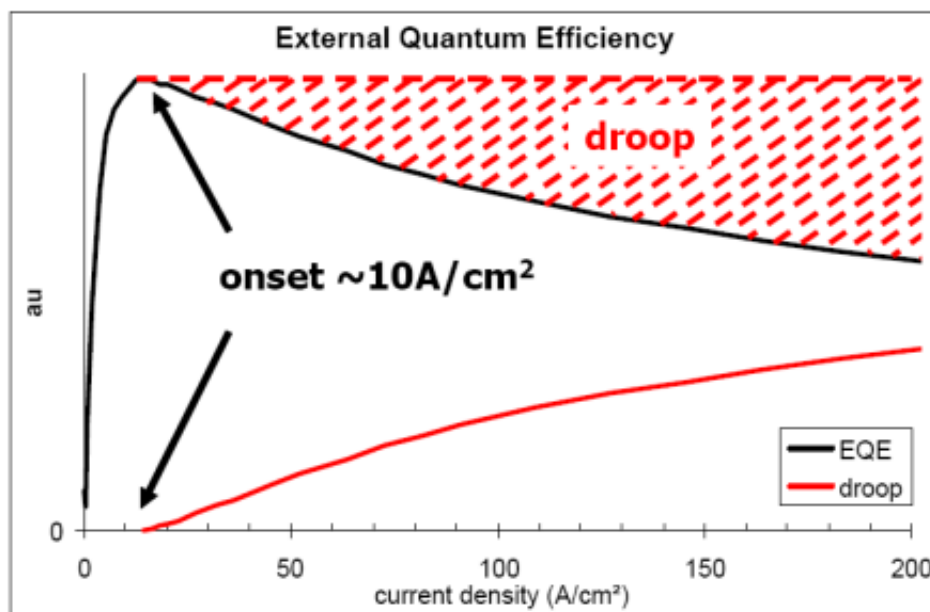
- Constant energy \rightarrow analyzer potentials fixed
- 50 meV resolution
- $\sim 3 \times 10^{-11}$ Torr ensures $\Phi_{GaN/Cs}$ stable over several days

Device Design

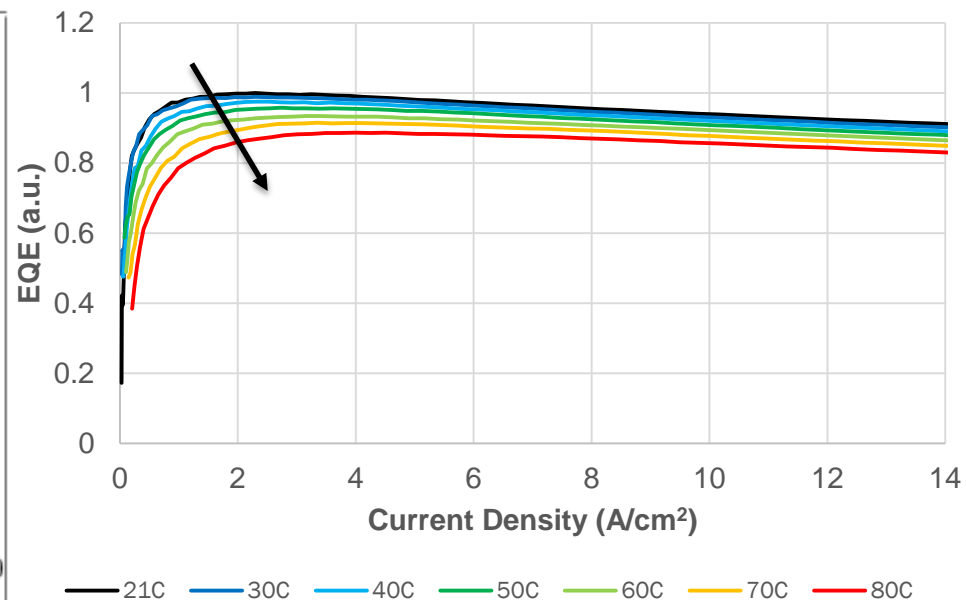


Impact

Current Droop



Thermal Droop



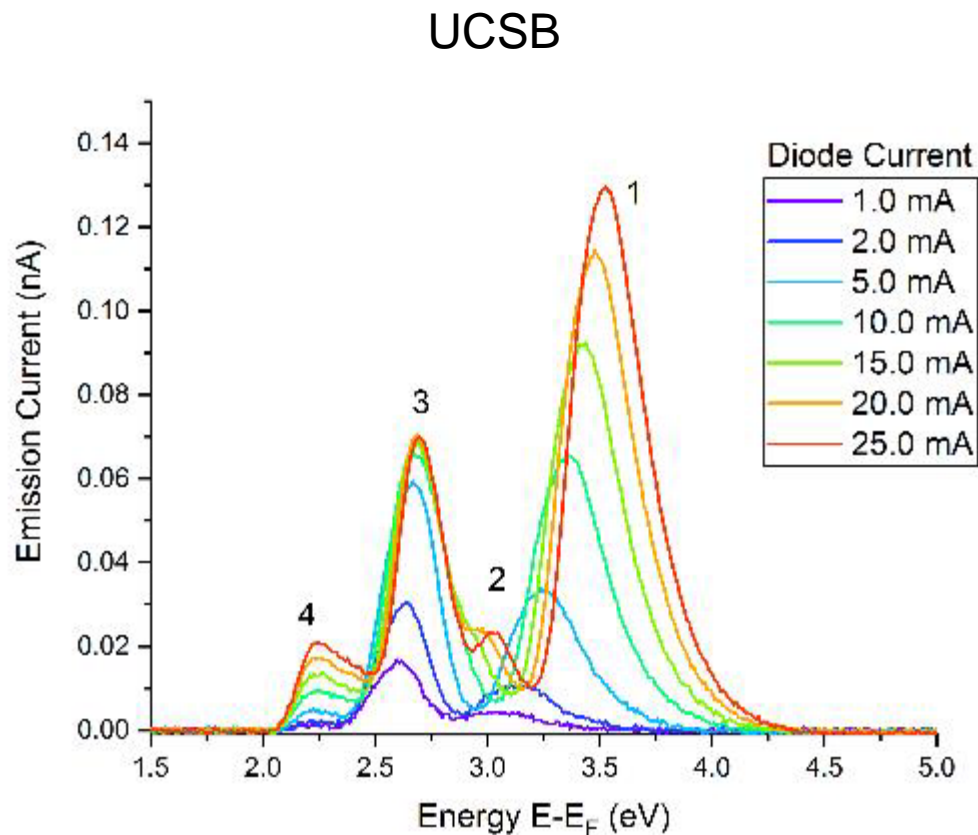
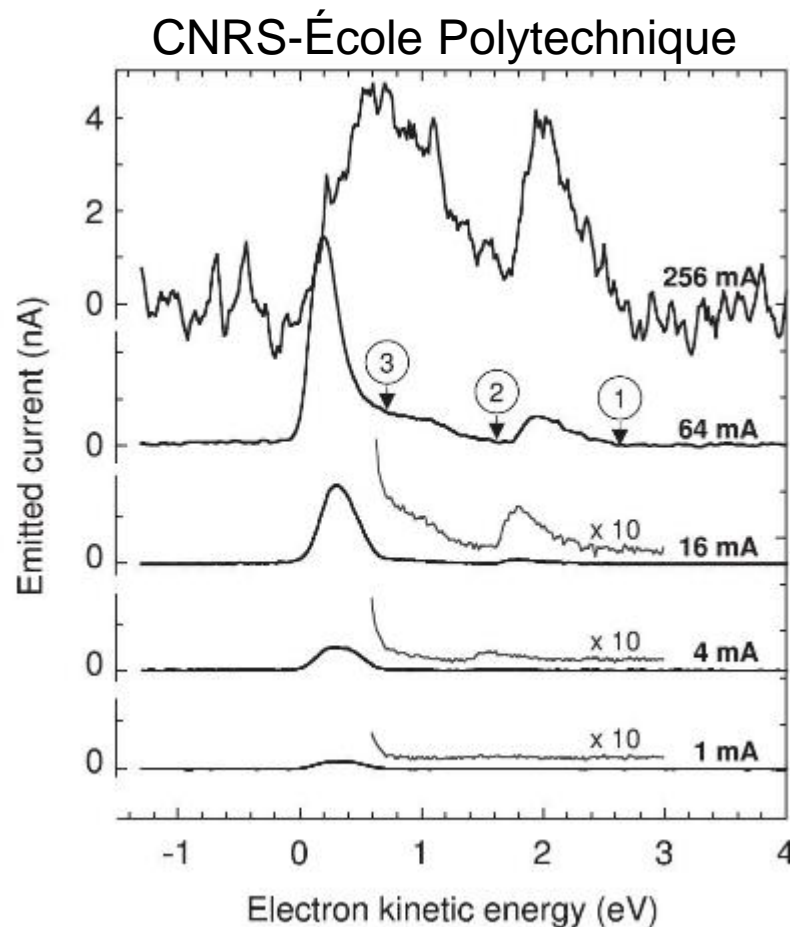
Advancement of LED technology by providing industry with physical mechanisms responsible for efficiency loss

- Understanding electron transport phenomena to optimize semiconductor design.
- Provide pathways for engineering solutions to efficiency problems in LEDs past current state-of-the-art.

Progress

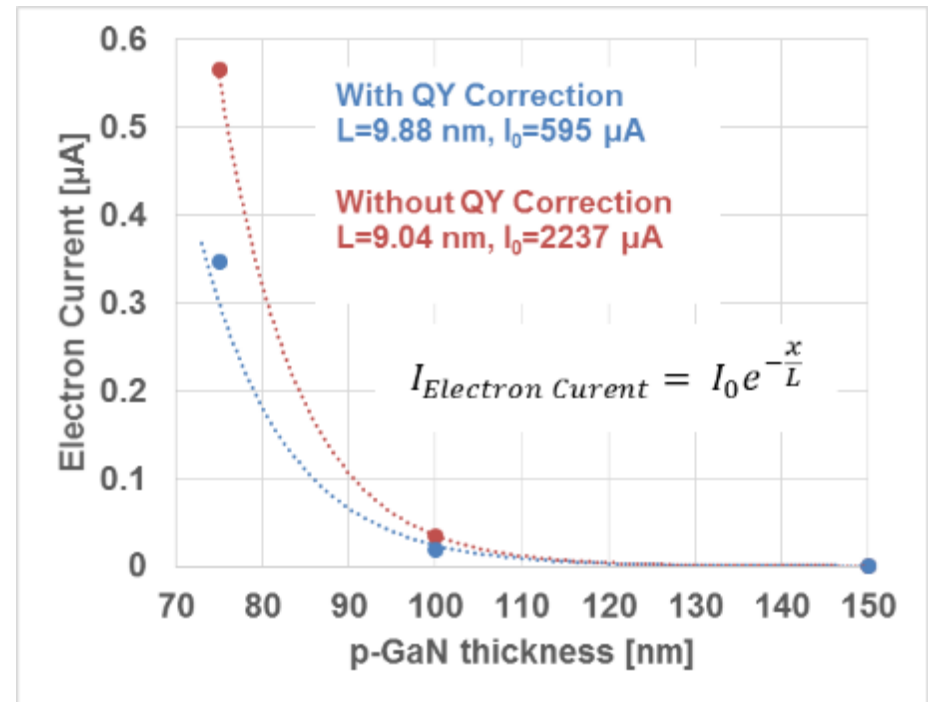
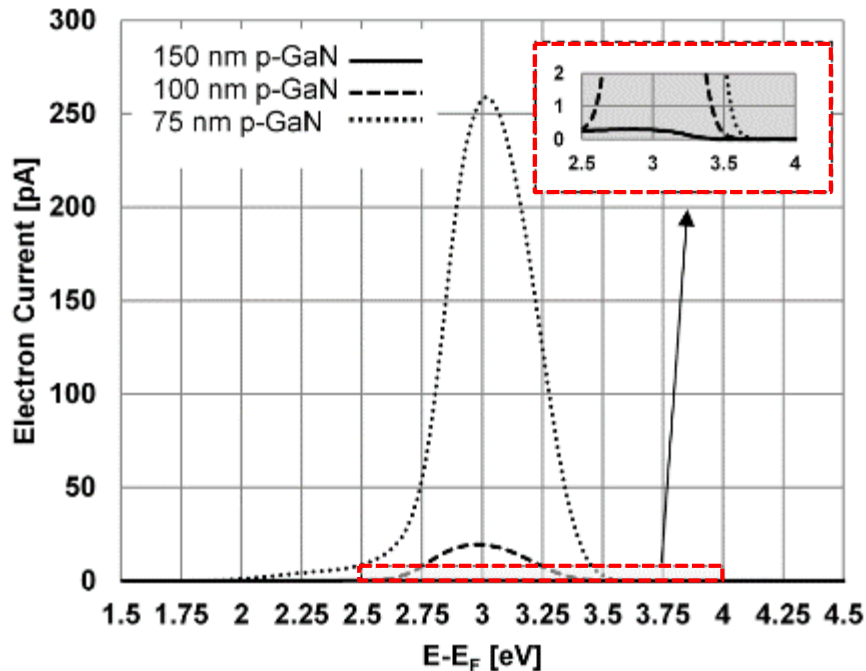
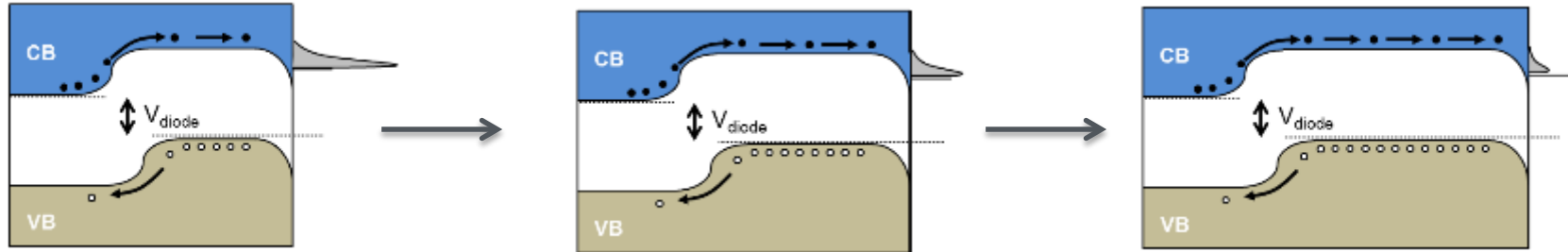
Subtask 3.1: EES on Commercial Grade Blue: Dominant Droop Mechanisms

UCSB confirms measurements of hot carriers emitted from LEDs.



Progress

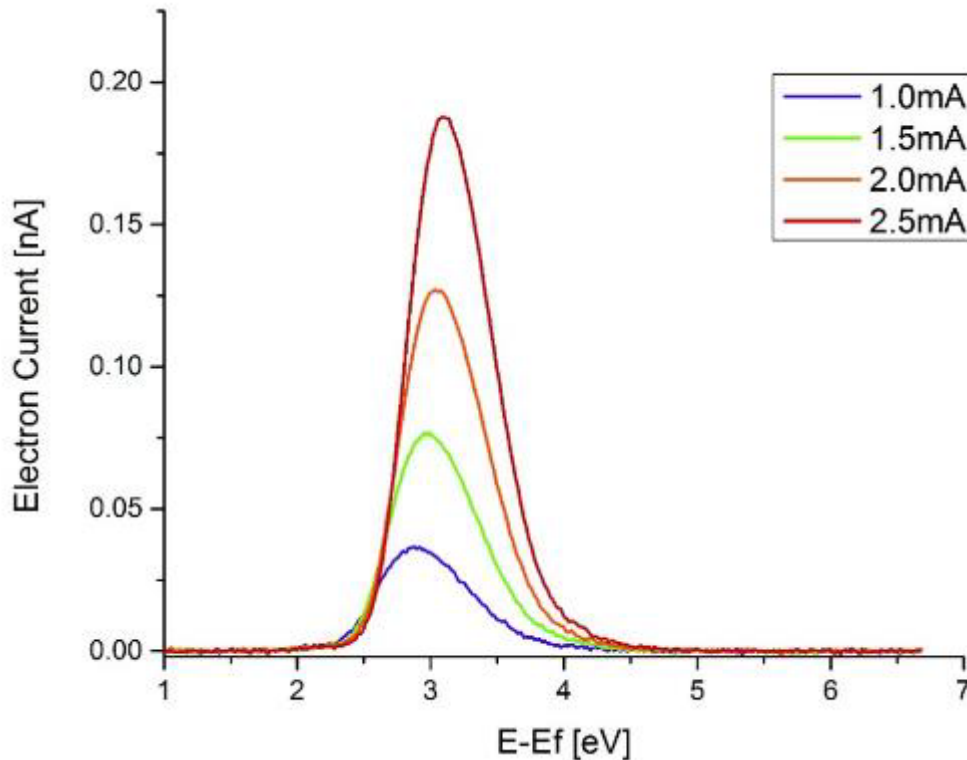
Milestone 2.1: Quantification of electron diffusion length in p-GaN



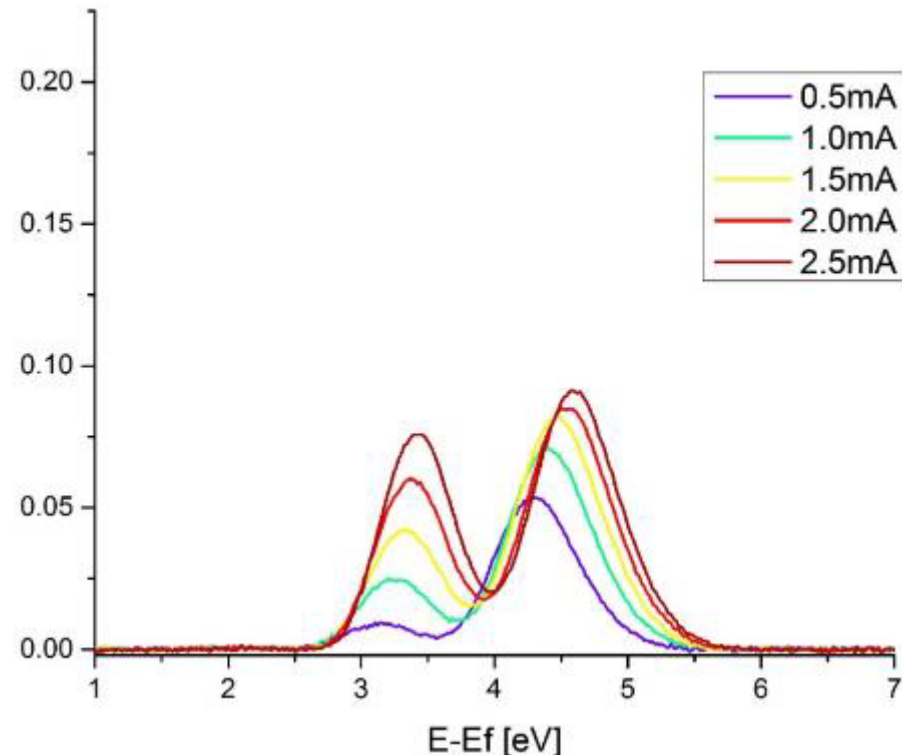
Progress

Milestone 2.2: Quantification of the efficacy of the AlGaN EBL via EE spectroscopy

P-n Junction, no EBL



P-n Junction, with EBL



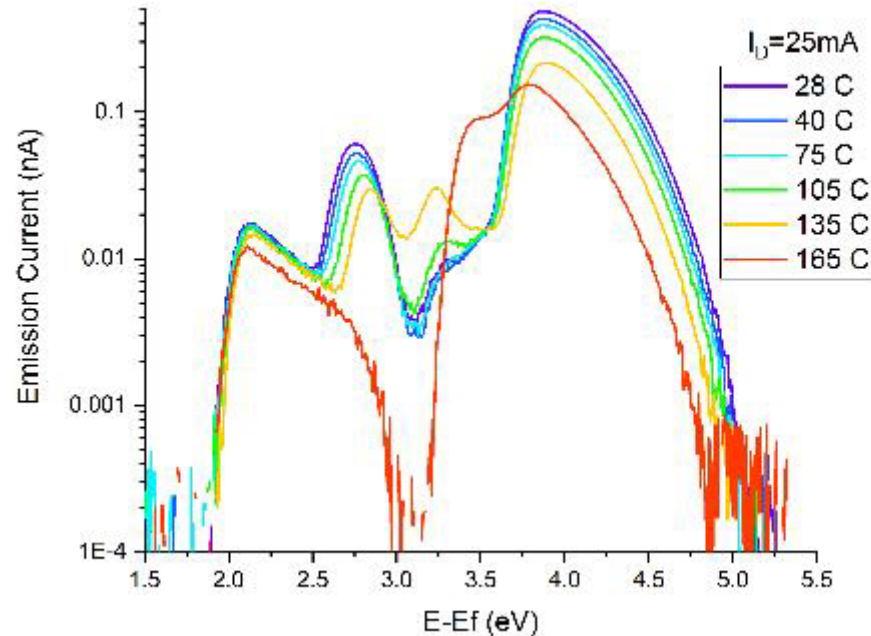
Electron blocking layer is capable of producing hot carriers.

- Only Γ -valley emission is seen from pn-junctions
- Hot carriers present in pn-junctions with EBLs may be generated by trap-assisted Auger recombination.

Progress

Milestone 3.3 & 5.4: EES to determine thermal droop mechanisms

Seoul LED 100nm p-GaN, no EBL

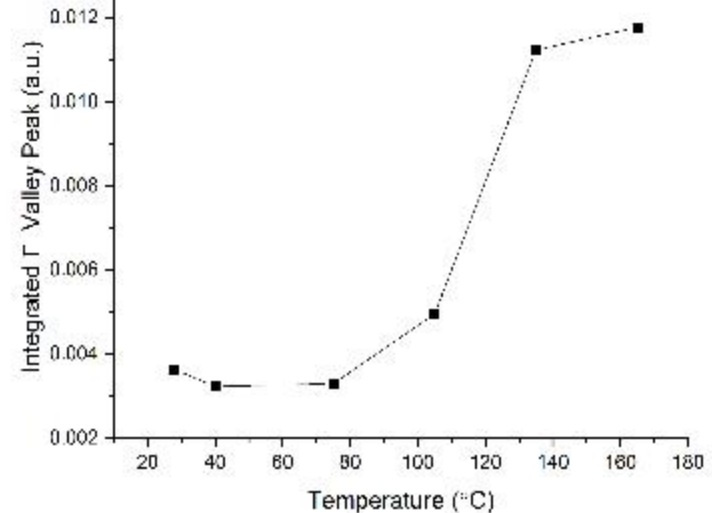


Temperature dependent EES

- Increases in Γ -valley electrons at temperatures above 75 °C suggests increases in QW overshoot and/or leakage.

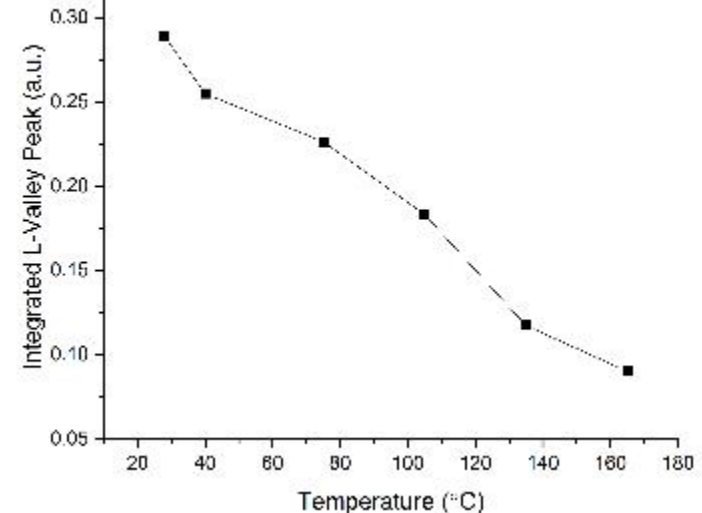
Γ -Valley Integrated Intensity vs Temperature

LED w/o EBL



Side Valley Integrated Intensity vs Temperature

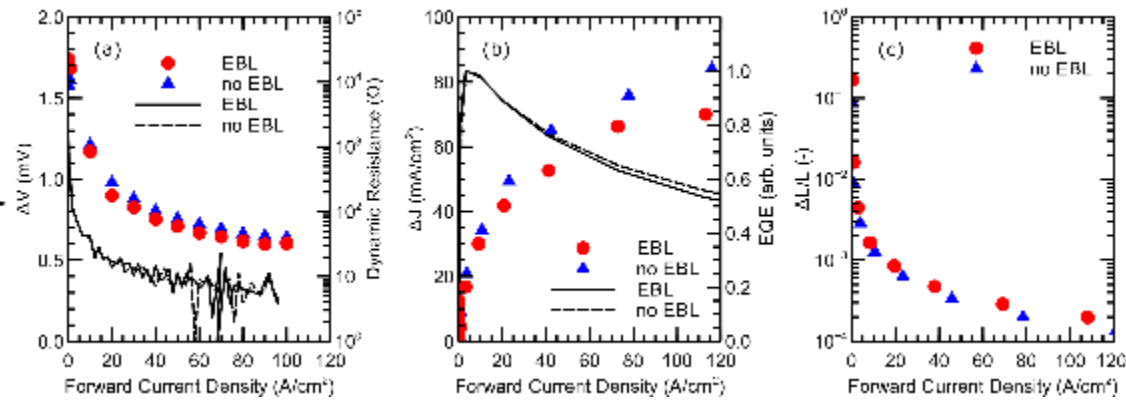
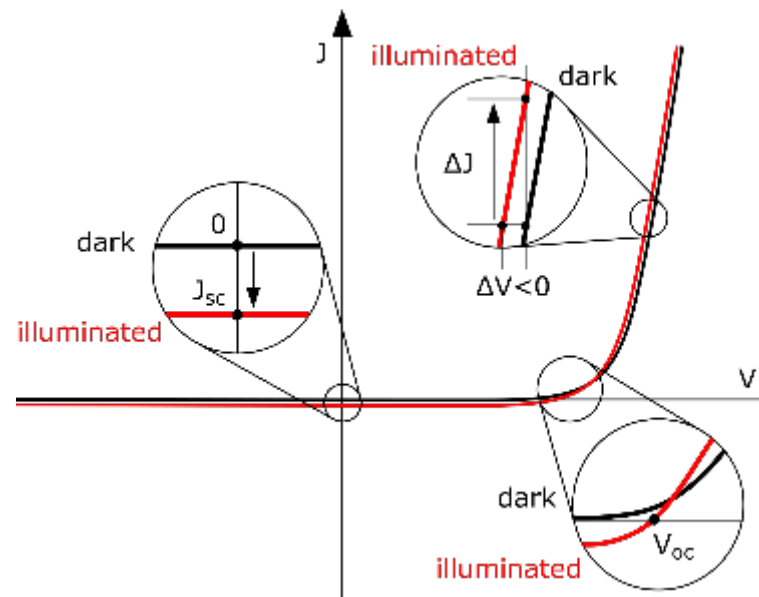
LED w/o EBL



Progress

Additional Work on Auger-Detection by Benchtop Photocurrent Measurements

Photocurrent in Forward-Biased LEDs
Increase in forward current (and EL intensity) in forward biased LEDs -> can only be explained by Auger-generated hot carrier current



APPLIED PHYSICS LETTERS **112**, 141106 (2018)



Auger-generated hot carrier current in photo-excited forward biased single quantum well blue light emitting diodes

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(Received 4 January 2018; accepted 22 March 2018; published online 3 April 2018)

Figures from **Espenlaub, et al., Appl. Phys. Lett., 112, 141106 (2018)** – recently published (Editor's Pick)

Stakeholder Engagement

Stakeholders:

U.S. Department of Energy

Cree, Inc. (U.S. industrial partner)

U.S. Academic R&D community

Engagement with Industry:

Industry partnerships have supplied sample material for the study of state-of-the-art devices. This provides us a pathway to understanding efficiency problems which persist in commercially available solid-state lighting.

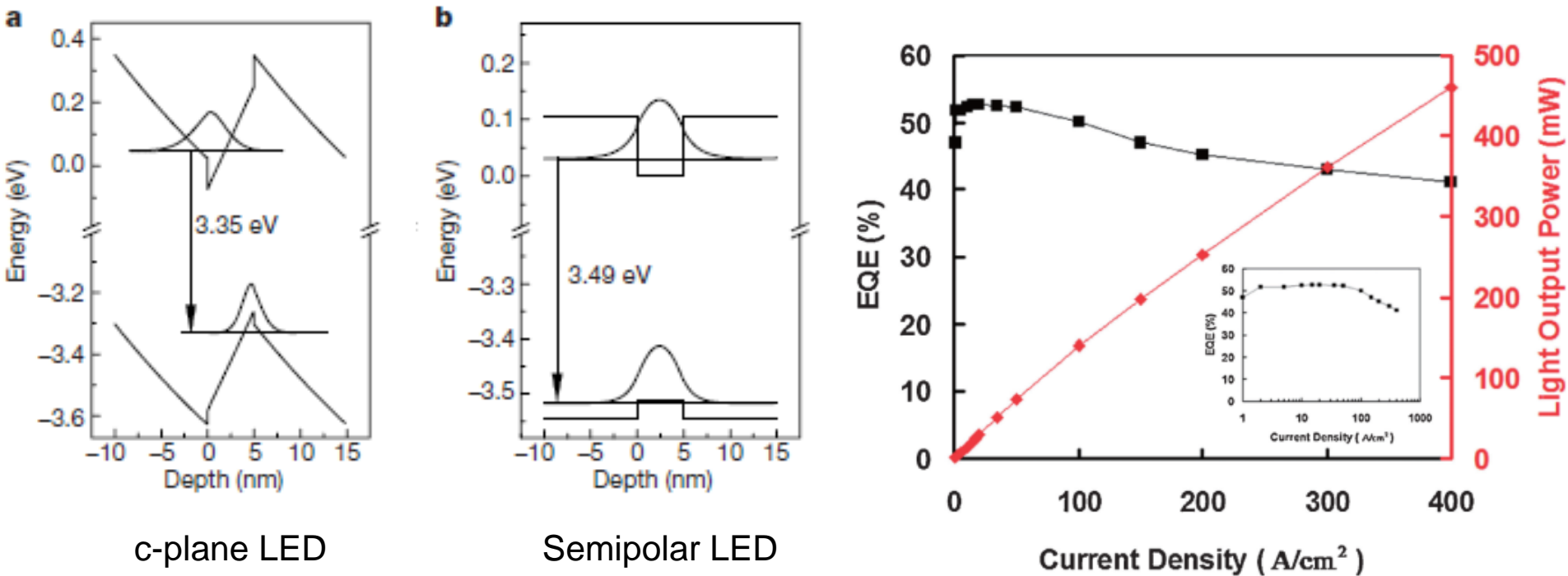
Communication with Stakeholders:

DoE SSL workshops

Scientific publications (recent article published in *Appl. Phys. Lett.*)

Remaining Project Work

Milestone 5.2: Identification of residual current droop mechanism in semipolar (2021) blue LEDs



EES measurements will provide explanation of low-droop characteristics of semipolar (2021) LEDs

- Improvements to wavefunction overlap by reduction of electric fields in active region.
- Reduction of QCSE → Reduced Auger recombination related efficiency losses.

Remaining Project Work

Milestone 5.2: Identification of residual current droop mechanism in semipolar (2021) blue LEDs

Growth details of reference pn-junctions and LEDs for EES experiments

pn-junctions

p++ contact layer ([Mg]=1.6e20)
p-GaN (<= 100nm) ([Mg]=1.0e19)
UID GaN
n++-GaN ([Si]=5.1e19)
n-GaN ([Si]=4.2e18)
20-2-1 Substrate

p++ contact layer
p-GaN
p-AlGaIn EBL
UID GaN
n++-GaN
n-GaN
20-2-1 Substrate

52 nm

LEDs

p++ contact layer
p-GaN
UID GaN
InGaIn SQW (~450nm)
UID GaN
n++-GaN
n-GaN
20-2-1 Substrate

p++ contact layer
p-GaN
p-AlGaIn EBL
UID GaN
InGaIn SQW (~450nm)
UID GaN
n++-GaN
n-GaN
20-2-1 Substrate

10 nm

85 nm

10 nm

14 nm

11 nm

27 nm

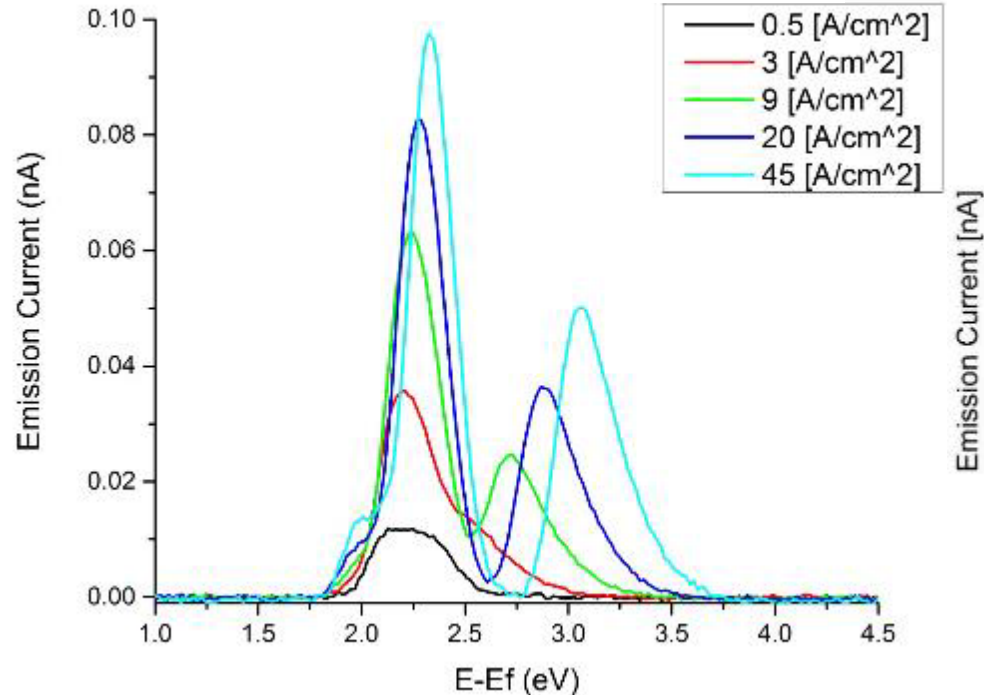
325 nm

1 um

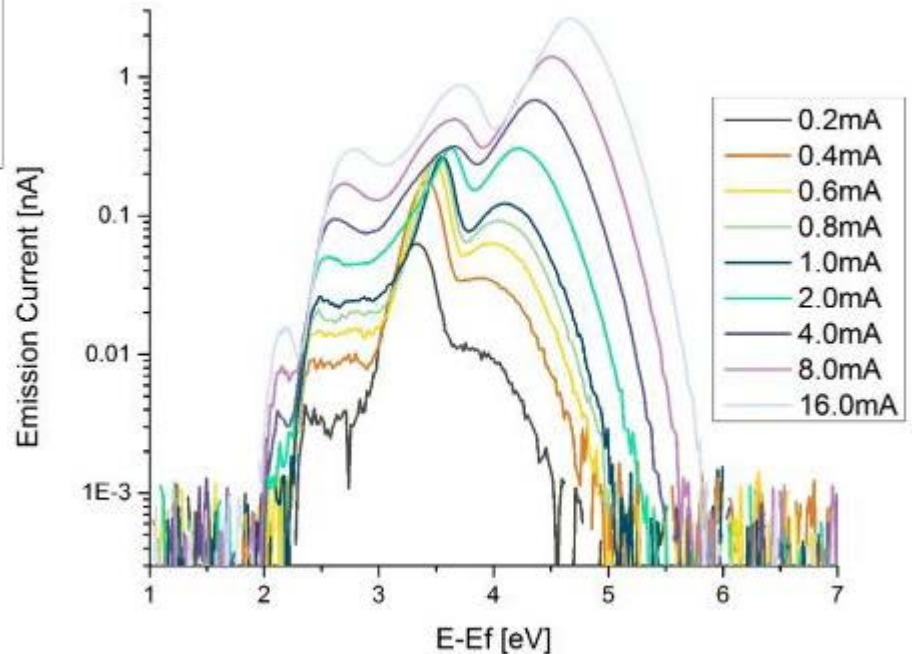
Remaining Project Work

Milestone 3.2: Determination of dominant droop mechanism in green LEDs

Industry Grown Green (520nm)



UCSB Green LED



Ongoing work towards understating droop mechanisms in green LEDs

- Large Γ -valley emission at low current density operation
- Auger generated electrons have lower energy in green \rightarrow possibly different intervalley transfer efficiency.

Thank You

UC Santa Barbara
Professor James S. Speck
Speck@ucsb.edu

REFERENCE SLIDES

Project Budget

Project Budget: FY 2018: No cost extension

Variances: One year no cost extension to complete tasks.

Cost to Date: \$935,245.34 to DOE ... estimated balance = \$0 on 6/30/2018

Additional Funding: None

Budget History

FY 2016 (past)		FY 2017 (past)		FY 2018 (current)	
DOE	Cost-share	DOE	Cost-share	DOE	Cost-share
550,000	137,495	450,001	112,505	NCE	NCE

Project Plan and Schedule

Project Schedule												
Project Start: July 31, 2015	Completed Work											
Projected End: July 31, 2018	Active Task (in progress work)											
	◆	Milestone/Deliverable (Planned)										
	◆	Milestone/Deliverable (Actual)										
	FY2016				FY2017				FY2018			
Task	Q1	Q2	Q3	Q4	Q1	Q2	Q3	Q4	Q1	Q2	Q3	Q4
Past Work												
Q1 Milestone 1.1: Annealable ohmic contacts to p-GaN	◆											
Q2 Milestone 1.2: Reduction in metal photoemission		◆										
Q3 Milestone 1.3: 1% quantum yield			◆									
Q4 Milestone 1.4: Quantum yields of Γ and L				◆								
Q4 Milestone 2.1: Electron diffusion length in p-GaN				◆								
Q4 Milestone 2.2: Efficacy of the AlGaIn EBL				◆								
Q4 Milestone 3.1: Dominant droop mechanism in blue LEDs				◆								
Q1 Milestone 1.5: 10% quantum yield			◆									
Q2 Milestone 1.6: Inter-valley transfer efficiencies					◆							
Q4 Milestone 3.3: Thermal droop c-plane in blue LEDs								◆				
Current/Future Work												
Q3 Milestone 1.7: 25% quantum yield								◆				◆
Q2 Milestone 3.2: Dominant droop mechanism in green LEDs					◆			◆				◆
Q3 Milestone 5.2: Droop mechanisms in semipolar blue LEDs							◆					◆
Q4 Milestone 5.4: Thermal droop in semipolar blue LEDs								◆				◆